Satoshi Yamasaki

List of Publications by Year
in descending order

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251 papers	5,822 citations	76196 40 h-index	118652 62 g-index
254 all docs	254 docs citations	254 times ranked	3794 citing authors

#	Article	IF	Citations
1	Germanium-Vacancy Single Color Centers in Diamond. Scientific Reports, 2015, 5, 12882.	1.6	251
2	Electrical and Structural Properties of Phosphorous-Doped Glow-Discharge Si:F:H and Si:H Films. Japanese Journal of Applied Physics, 1980, 19, L305-L308.	0.8	189
3	n-type doping of (001)-oriented single-crystalline diamond by phosphorus. Applied Physics Letters, 2005, 86, 222111.	1.5	172
4	Inversion channel diamond metal-oxide-semiconductor field-effect transistor with normally off characteristics. Scientific Reports, 2016, 6, 31585.	1.6	150
5	Effects of the anti-interleukin-6 receptor antibody, tocilizumab, on serum lipid levels in patients with rheumatoid arthritis. Rheumatology International, 2011, 31, 451-456.	1.5	100
6	Indium-Catalyzed Direct Chlorination of Alcohols Using Chlorodimethylsilaneâ€ Benzil as a Selective and Mild System. Journal of the American Chemical Society, 2004, 126, 7186-7187.	6.6	92
7	Optical absorption edge of hydrogenated amorphous silicon studied by photoacoustic spectroscopy. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1987, 56, 79-97.	0.6	90
8	n-type diamond growth by phosphorus doping on (0â€‰0â€‰1)-oriented surface. Journal Physics D: Applied Physics, 2007, 40, 6189-6200.	1.3	90
9	Misorientation-angle dependence of boron incorporation into (001)-oriented chemical-vapor-deposited (CVD) diamond. Journal of Crystal Growth, 2011, 317, 60-63.	0.7	90
10	Electron-spin phase relaxation of phosphorus donors in nuclear-spin-enriched silicon. Physical Review B, 2004, 70, .	1.1	89
11	Perfect selective alignment of nitrogen-vacancy centers in diamond. Applied Physics Express, 2014, 7, 055201.	1.1	84
12	Direct Nanoscale Sensing of the Internal Electric Field in Operating Semiconductor Devices Using Single Electron Spins. ACS Nano, 2017, 11, 1238-1245.	7.3	82
13	Boron Doping of Hydrogenated Silicon Thin Films. Japanese Journal of Applied Physics, 1981, 20, L183-L186.	0.8	80
14	Diamond Schottky-pn diode with high forward current density and fast switching operation. Applied Physics Letters, 2009, 94, .	1.5	77
15	Pure negatively charged state of the NV center in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math>-type diamond. Physical Review B, 2016, 93, .	1.1	77
16	CD4+CD25^{high}CD127^{low/-} Treg Cell Frequency from Peripheral Blood Correlates with Disease Activity in Patients with Rheumatoid Arthritis. Journal of Rheumatology, 2011, 38, 2517-2521.	1.0	74
17	600 V Diamond Junction Field-Effect Transistors Operated at 200$^{circ}{m C}$. IEEE Electron Device Letters, 2014, 35, 241-243.	2.2	74
18	High performance of diamond p+-i-n+ junction diode fabricated using heavily doped p+ and n+ layers. Applied Physics Letters, 2009, 94, .	1.5	73

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19	Enhancement in emission efficiency of diamond deep-ultraviolet light emitting diode. Applied Physics Letters, 2011, 99, .	1.5	73
20	Pulsed-ESR study of light-induced metastable defect in a-Si:H. Journal of Non-Crystalline Solids, 1993, 164-166, 169-174.	1.5	69
21	Low specific contact resistance of heavily phosphorus-doped diamond film. Applied Physics Letters, 2008, 93, .	1.5	68
22	Tunable light emission from nitrogen-vacancy centers in single crystal diamond PIN diodes. Applied Physics Letters, 2013, 102, .	1.5	62
23	Diamond Junction Field-Effect Transistors with Selectively Grown n^{+}-Side Gates. Applied Physics Express, 2012, 5, 091301.	1.1	61
24	Diamond foam electrodes for electrochemical applications. Electrochemistry Communications, 2013, 33, 88-91.	2.3	57
25	Selective Growth of Buried n+Diamond on (001) Phosphorus-Doped n-Type Diamond Film. Applied Physics Express, 2009, 2, 055502.	1.1	55
26	High-Efficiency Excitonic Emission with Deep-Ultraviolet Light from (001)-Oriented Diamondp-i-nJunction. Japanese Journal of Applied Physics, 2006, 45, L1042-L1044.	0.8	52
27	Electrical characterization of diamond Pi<scp>N</scp> diodes for high voltage applications. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 2035-2039.	0.8	52
28	Diamond bipolar junction transistor device with phosphorus-doped diamond base layer. Diamond and Related Materials, 2012, 27-28, 19-22.	1.8	51
29	High-Temperature Operation of Diamond Junction Field-Effect Transistors With Lateral p-n Junctions. IEEE Electron Device Letters, 2013, 34, 1175-1177.	2.2	51
30	Doping and interface of homoepitaxial diamond for electronic applications. MRS Bulletin, 2014, 39, 499-503.	1.7	49
31	N-type control of single-crystal diamond films by ultra-lightly phosphorus doping. Applied Physics Letters, 2016, 109, .	1.5	49
32	Local structure of Ge nanoislands on Si(111) surfaces with a SiO2 coverage. Applied Physics Letters, 2001, 78, 2563-2565.	1.5	47
33	Growth of amorphous-layer-free microcrystalline silicon on insulating glass substrates by plasma-enhanced chemical vapor deposition. Applied Physics Letters, 1997, 71, 1534-1536.	1.5	46
34	Structural Study on Amorphous-Microcrystalline Mixed-Phase Si:H Films. Japanese Journal of Applied Physics, 1981, 20, L439-L442.	0.8	45
35	Ohmic contacts on p-type homoepitaxial diamond and their thermal stability. Semiconductor Science and Technology, 2005, 20, 860-863.	1.0	44
36	Atomically flat diamond (111) surface formation by homoepitaxial lateral growth. Diamond and Related Materials, 2008, 17, 1051-1054.	1.8	43

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37	Generation and transportation mechanisms for two-dimensional hole gases in GaN/AlGaN/GaN double heterostructures. Journal of Applied Physics, 2014, 115, .	1.1	42
38	Anisotropic diamond etching through thermochemical reaction between Ni and diamond in high-temperature water vapour. Scientific Reports, 2018, 8, 6687.	1.6	41
39	Determination of the Optical Constants of Thin Films Using Photoacoustic Spectroscopy. Japanese Journal of Applied Physics, 1981, 20, L665-L668.	0.8	40
40	Cage-Shaped Borate Esters with Enhanced Lewis Acidity and Catalytic Activity. Organic Letters, 2006, 8, 761-764.	2.4	40
41	Surface reactions during etching of organic low-k films by plasmas of N2 and H2. Journal of Applied Physics, 2006, 99, 083305.	1.1	40
42	Carrier compensation in (001) n-type diamond by phosphorus doping. Diamond and Related Materials, 2007, 16, 796-799.	1.8	40
43	Atomistic mechanism of perfect alignment of nitrogen-vacancy centers in diamond. Applied Physics Letters, 2014, 105, .	1.5	39
44	Origin of type-Cdefects on theSi(100)â˜'(2Ã—1)surface. Physical Review B, 2002, 65, .	1.1	38
45	Fabrication of bipolar junction transistor on (001)-oriented diamond by utilizing phosphorus-doped n-type diamond base. Diamond and Related Materials, 2013, 34, 41-44.	1.8	38
46	Surface roughening of diamond (001) films during homoepitaxial growth in heavy boron doping. Diamond and Related Materials, 2007, 16, 767-770.	1.8	37
47	Cutaneous vasculitis induced by TNF inhibitors: a report of three cases. Modern Rheumatology, 2010, 20, 86-89.	0.9	37
48	Diamond Schottky-pn diode using lightly nitrogen-doped layer. Diamond and Related Materials, 2017, 75, 152-154.	1.8	37
49	Normally-Off Diamond Junction Field-Effect Transistors With Submicrometer Channel. IEEE Electron Device Letters, 2016, 37, 209-211.	2.2	36
50	Characterization of specific contact resistance on heavily phosphorus-doped diamond films. Diamond and Related Materials, 2009, 18, 782-785.	1.8	35
51	High serum matrix metalloproteinase 3 is characteristic of patients with paraneoplastic remitting seronegative symmetrical synovitis with pitting edema syndrome. Modern Rheumatology, 2012, 22, 584-588.	0.9	35
52	Gap-State Profiles of a-Si: H Deduced from Below-Gap Optical Absorption. Japanese Journal of Applied Physics, 1982, 21, L539-L541.	0.8	34
53	Diamond Schottkyâ€pn diode without tradeâ€off relationship between onâ€resistance and blocking voltage. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 2105-2109.	0.8	34
54	Growth of atomically step-free surface on diamond {111} mesas. Diamond and Related Materials, 2010, 19, 288-290.	1.8	33

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55	Electrical excitation of silicon-vacancy centers in single crystal diamond. Applied Physics Letters, 2015, 106, .	1.5	33
56	In situelectron-spin-resonance measurements of film growth of hydrogenated amorphous silicon. Applied Physics Letters, 1997, 70, 1137-1139.	1.5	32
57	Control of crystallinity of microcrystalline silicon film grown on insulating glass substrates. Journal of Non-Crystalline Solids, 1998, 227-230, 857-860.	1.5	32
58	Electrical properties of lateral pâ€“n junction diodes fabricated by selective growth of n⁺ diamond. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1761-1764.	0.8	32
59	Electronic properties of diamond Schottky barrier diodes fabricated on silicon-based heteroepitaxially grown diamond substrates. Applied Physics Express, 2015, 8, 104103.	1.1	30
60	Electrical and lightâ€emitting properties of homoepitaxial diamond pâ€“iâ€“n junction. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 2200-2206.	0.8	29
61	Electrical activity of doped phosphorus atoms in (001) nâ€type diamond. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 2195-2199.	0.8	29
62	Diamond electronic devices fabricated using heavily doped hopping p⁺and n⁺layers. Japanese Journal of Applied Physics, 2014, 53, 05FA12.	0.8	29
63	Hillock-Free Heavily Boron-Doped Homoepitaxial Diamond Films on Misoriented (001) Substrates. Japanese Journal of Applied Physics, 2007, 46, 1469-1470.	0.8	28
64	(Invited) Optical, Electrical and Structural Properties of Plasma-Deposited Amorphous Silicon. Japanese Journal of Applied Physics, 1981, 20, 267.	0.8	27
65	Reduction of plasma-induced damage in SiO[sub 2] films during pulse-time-modulated plasma irradiation. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 389.	1.6	27
66	Disease activity score 28 may overestimate the remission induction of rheumatoid arthritis patients treated with tocilizumab: comparison with the remission by the clinical disease activity index. Modern Rheumatology, 2011, 21, 365-369.	0.9	27
67	High-Temperature Bipolar-Mode Operation of Normally-Off Diamond JFET. IEEE Journal of the Electron Devices Society, 2017, 5, 95-99.	1.2	27
68	Single crystal diamond membranes for nanoelectronics. Nanoscale, 2018, 10, 4028-4035.	2.8	27
69	Cageâ€Shaped Borate Esters with Tris(2â€oxyphenyl)methane or â€silane System Frameworks Bearing Multiple Tuning Factors: Geometric and Substituent Effects on Their Lewis Acid Properties. Chemistry - A European Journal, 2011, 17, 3856-3867.	1.7	26
70	Calculation of Lattice Constant of 4H-SiC as a Function of Impurity Concentration. Materials Science Forum, 0, 645-648, 247-250.	0.3	25
71	Nucleation and coalescence in hydrogenated amorphous silicon studied by scanning tunneling microscopy. Applied Physics Letters, 1994, 65, 1760-1762.	1.5	24
72	Hydrogen plasma etching mechanism on (001) diamond. Journal of Crystal Growth, 2006, 293, 311-317.	0.7	24

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73	Electron Emission from a Diamond (111) pâ€“iâ€“n+Junction Diode with Negative Electron Affinity during Room Temperature Operation. Applied Physics Express, 2010, 3, 041301.	1.1	24
74	Homoepitaxial diamond pâ€“n+ junction with low specific on-resistance and ideal built-in potential. Diamond and Related Materials, 2008, 17, 782-785.	1.8	23
75	Large improvement of phosphorus incorporation efficiency in n-type chemical vapor deposition of diamond. Applied Physics Letters, 2014, 105, .	1.5	23
76	Heavily phosphorus-doped nano-crystalline diamond electrode for thermionic emission application. Diamond and Related Materials, 2016, 63, 165-168.	1.8	23
77	Formation of atomically flat hydroxyl-terminated diamond (1â€¯1â€¯1) surfaces via water vapor annealing. Applied Surface Science, 2018, 458, 222-225.	3.1	23
78	Electron Spin Resonance Observation of the Si(111)-(7Ã—7)Surface and Its Oxidation Process. Physical Review Letters, 2001, 86, 1054-1057.	2.9	22
79	Growth and characterization of phosphorus-doped diamond using organophosphorus gases. Physica Status Solidi A, 2005, 202, 2122-2128.	1.7	22
80	Strong Excitonic Emission from (001)-Oriented DiamondP-NJunction. Japanese Journal of Applied Physics, 2005, 44, L1190-L1192.	0.8	22
81	Fabrication of graphene on atomically flat diamond (111) surfaces using nickel as a catalyst. Diamond and Related Materials, 2017, 75, 105-109.	1.8	22
82	Mechanism of anisotropic etching on diamond (111) surfaces by a hydrogen plasma treatment. Applied Surface Science, 2017, 422, 452-455.	3.1	22
83	High-Voltage Vacuum Switch with a Diamond pâ€“iâ€“n Diode Using Negative Electron Affinity. Japanese Journal of Applied Physics, 2012, 51, 090113.	0.8	22
84	Electrical and optical characterization of boron-doped (111) homoepitaxial diamond films. Diamond and Related Materials, 2005, 14, 1964-1968.	1.8	21
85	Emission properties from dense exciton gases in diamond. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 3226-3244.	0.8	21
86	Early diagnosis and treatment for remission of clinically amyopathic dermatomyositis complicated by rapid progress interstitial lung disease: a report of two cases. Modern Rheumatology, 2013, 23, 190-194.	0.9	21
87	Upregulation of Thrombospondin 1 Expression in Synovial Tissues and Plasma of Rheumatoid Arthritis: Role of Transforming Growth Factor-Î²1 toward Fibroblast-like Synovial Cells. Journal of Rheumatology, 2015, 42, 943-947.	1.0	21
88	In vacuo measurements of dangling bonds created during Ar-diluted fluorocarbon plasma etching of silicon dioxide films. Applied Physics Letters, 2005, 86, 264104.	1.5	20
89	Growth of phosphorus-doped diamond using tertiarybutylphosphine and trimethylphosphine as dopant gases. Diamond and Related Materials, 2005, 14, 340-343.	1.8	20
90	N-type doping on (001)-oriented diamond. Diamond and Related Materials, 2006, 15, 548-553.	1.8	20

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91	Surface conductive layers on (111) diamonds after oxygen treatments. Diamond and Related Materials, 2006, 15, 692-697.	1.8	20
92	Prediction of DAS28-ESR remission at 6 months by baseline variables in patients with rheumatoid arthritis treated with etanercept in Japanese population. Modern Rheumatology, 2009, 19, 488-492.	0.9	20
93	Diamond Schottky pâ€“n diode with high forward current density. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2086-2090.	0.8	20
94	Nanometer Scale Height Standard Using Atomically Controlled Diamond Surface. Applied Physics Express, 0, 2, 055001.	1.1	20
95	Energy level of compensator states in (001) phosphorus-doped diamond. Diamond and Related Materials, 2011, 20, 1016-1019.	1.8	20
96	Energy distribution of Al2O3/diamond interface states characterized by high temperature capacitance-voltage method. Carbon, 2020, 168, 659-664.	5.4	20
97	Interpretation of29Si nuclear magnetic resonance spectra of amorphous hydrogenated silicon. Journal of Applied Physics, 1986, 60, 1839-1841.	1.1	19
98	Creation and annihilation mechanism of dangling bonds within the a-Si:H growth surface studied by in situ ESR technique. Journal of Non-Crystalline Solids, 2000, 266-269, 529-533.	1.5	19
99	Observation of oscillating behavior in the reflectance difference spectra of oxidized Si(001) surfaces. Journal of Applied Physics, 2002, 91, 3637-3643.	1.1	19
100	Surface conductive layers on oxidized (111) diamonds. Applied Physics Letters, 2005, 87, 262107.	1.5	19
101	Formation of Step-Free Surfaces on Diamond (111) Mesas by Homoepitaxial Lateral Growth. Japanese Journal of Applied Physics, 2012, 51, 090107.	0.8	19
102	Carrier transport in homoepitaxial diamond films with heavy phosphorus doping. Japanese Journal of Applied Physics, 2014, 53, 05FP05.	0.8	19
103	Inversion channel mobility and interface state density of diamond MOSFET using N-type body with various phosphorus concentrations. Applied Physics Letters, 2019, 114, .	1.5	19
104	Prediction of DAS28-ESR remission at 6Âmonths by baseline variables in patients with rheumatoid arthritis treated with etanercept in Japanese population. Modern Rheumatology, 2009, 19, 488-492.	0.9	19
105	Formation of Step-Free Surfaces on Diamond (111) Mesas by Homoepitaxial Lateral Growth. Japanese Journal of Applied Physics, 2012, 51, 090107.	0.8	19
106	Proton nuclear magnetic resonance study on hydrogen incorporation in amorphousâ€microcrystalline mixedâ€phase hydrogenated silicon. Journal of Applied Physics, 1984, 56, 2658-2663.	1.1	18
107	Control of photodegradation in amorphous silicon: The effect of deuterium. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1991, 63, 281-292.	0.6	18
108	n-type conductivity of phosphorus-doped homoepitaxial single crystal diamond on (001) substrate. Diamond and Related Materials, 2005, 14, 2007-2010.	1.8	18

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109	Electrical and light-emitting properties of (001)-oriented homoepitaxial diamond pâ€“iâ€“n junction. Diamond and Related Materials, 2007, 16, 1025-1028.	1.8	18
110	Electrical and light-emitting properties from (111)-oriented homoepitaxial diamond pâ€“iâ€“n junctions. Diamond and Related Materials, 2009, 18, 764-767.	1.8	18
111	Reduction in serum levels of substance P in patients with rheumatoid arthritis by etanercept, a tumor necrosis factor inhibitor. Modern Rheumatology, 2011, 21, 244-250.	0.9	17
112	High-Voltage Vacuum Switch with a Diamond pâ€“iâ€“n Diode Using Negative Electron Affinity. Japanese Journal of Applied Physics, 2012, 51, 090113.	0.8	17
113	Vector Electrometry in a Wide-Gap-Semiconductor Device Using a Spin-Ensemble Quantum Sensor. Physical Review Applied, 2020, 14, .	1.5	17
114	Self-Heating Effects in Long Superconducting Thin Films over a Wide Temperature Range. Japanese Journal of Applied Physics, 1979, 18, 667-670.	0.8	16
115	Ab initio energetics of phosphorus related complex defects in synthetic diamond. Physica B: Condensed Matter, 2006, 376-377, 304-306.	1.3	16
116	Plasma-Induced Deterioration of Mechanical Characteristics of Microcantilever. Japanese Journal of Applied Physics, 2010, 49, 04DL20.	0.8	16
117	Multiple phosphorus chemical sites in heavily phosphorus-doped diamond. Applied Physics Letters, 2011, 98, .	1.5	16
118	In rheumatoid arthritis patients treated with tocilizumab, the rate of clinical disease activity index (CDAI) remission at 24 weeks is superior in those with higher titers of IgM-rheumatoid factor at baseline. Modern Rheumatology, 2011, 21, 370-374.	0.9	16
119	Reduction of nâ€type diamond contact resistance by graphite electrode. Physica Status Solidi - Rapid Research Letters, 2014, 8, 137-140.	1.2	16
120	A Photoluminescence Study of Amorphous-Microcrystalline Mixed-Phase Si:H Films. Japanese Journal of Applied Physics, 1981, 20, L793-L796.	0.8	15
121	Electrical and optical characterizations of (001)-oriented homoepitaxial diamond pâ€“n junction. Diamond and Related Materials, 2006, 15, 513-516.	1.8	15
122	Fermi level pinning-free interface at metals/homoepitaxial diamond (111) films after oxidation treatments. Applied Physics Letters, 2008, 92, 112112.	1.5	14
123	Roughening of atomically flat diamond (111) surfaces by a hot HNO3/H2SO4 solution. Diamond and Related Materials, 2008, 17, 486-488.	1.8	14
124	Generation and reduction in SiO2/Si interface state density during plasma etching processes. Journal of Applied Physics, 2008, 104, 063308.	1.1	14
125	Magnetic Resonance Imaging Bone Edema at Enrollment Predicts Rapid Radiographic Progression in Patients with Early RA: Results from the Nagasaki University Early Arthritis Cohort. Journal of Rheumatology, 2016, 43, 1278-1284.	1.0	14
126	Direct observation of inversion capacitance in p-type diamond MOS capacitors with an electron injection layer. Japanese Journal of Applied Physics, 2018, 57, 04FR01.	0.8	14

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127	Disease activity score 28 may overestimate the remission induction of rheumatoid arthritis patients treated with tocilizumab: comparison with the remission by the clinical disease activity index. Modern Rheumatology, 2011, 21, 365-369.	0.9	14
128	NMR study of Î¼c-Si:H. Journal of Non-Crystalline Solids, 1983, 59-60, 779-782.	1.5	13
129	Si29nuclear magnetic resonance of amorphous hydrogenated silicon and amorphous microcrystalline mixed-phase hydrogenated silicon. Physical Review B, 1987, 35, 4581-4590.	1.1	13
130	Microscopic origin of light-induced ESR centers in undoped hydrogenated amorphous silicon. Physical Review B, 2000, 62, 15702-15710.	1.1	13
131	ESR Characterization of SiC Bulk Crystals and SiO₂/SiC Interface. Materials Science Forum, 2002, 389-393, 1025-1028.	0.3	13
132	Nonlinear behavior of currentâ€dependent emission for diamond lightâ€emitting diodes. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1754-1760.	0.8	13
133	Inversion-type p-channel diamond MOSFET issues. Journal of Materials Research, 2021, 36, 4688-4702.	1.2	13
134	Switching to the anti-interleukin-6 receptor antibody tocilizumab in rheumatoid arthritis patients refractory to antitumor necrosis factor biologics. Modern Rheumatology, 2010, 20, 40-45.	0.9	13
135	Atomic-layer resolved monitoring of thermal oxidation of Si(001) by reflectance difference oscillation technique. Thin Solid Films, 2004, 455-456, 759-763.	0.8	12
136	Flattening of oxidized diamond (111) surfaces with H2SO4/H2O2 solutions. Diamond and Related Materials, 2009, 18, 213-215.	1.8	12
137	Improvement of (001)-oriented diamond p-i-n diode by use of selective grown n+ layer. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 2099-2104.	0.8	12
138	Comparative Evaluation of Ultrathin Mask Layers of SiO2, SiOxNyand SiNxfor Selective Area Growth of Si. Japanese Journal of Applied Physics, 1998, 37, 4204-4208.	0.8	11
139	Leakage Current Distribution of Cu-Contaminated Thin SiO2. Japanese Journal of Applied Physics, 2003, 42, L160-L162.	0.8	11
140	Low-damage fabrication of high aspect nanocolumns by using neutral beams and ferritin-iron-core mask. Journal of Vacuum Science & Technology B, 2007, 25, 760.	1.3	11
141	The role of boron atoms in heavily boron-doped semiconducting homoepitaxial diamond growth â€" Study of surface morphology. Diamond and Related Materials, 2007, 16, 409-411.	1.8	11
142	Development of Low-AC-Loss Bi-2223 Superconducting Multifilamentary Wires. IEEE Transactions on Applied Superconductivity, 2009, 19, 3053-3056.	1.1	11
143	Switching to the anti-interleukin-6 receptor antibody tocilizumab in rheumatoid arthritis patients refractory to antitumor necrosis factor biologics. Modern Rheumatology, 2010, 20, 40-45.	0.9	11
144	High-Performance Three-Terminal Fin Field-Effect Transistors Fabricated by a Combination of Damage-Free Neutral-Beam Etching and Neutral-Beam Oxidation. Japanese Journal of Applied Physics, 2010, 49, 04DC17.	0.8	11

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145	Desorption time of phosphorus during MPCVD growth of n-type (001) diamond. Diamond and Related Materials, 2016, 64, 208-212.	1.8	11
146	Estimation of Inductively Coupled Plasma Etching Damage of Boronâ€Doped Diamond Using Xâ€Ray Photoelectron Spectroscopy. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700233.	0.8	11
147	Temperature dependence of electrical characteristics for diamond Schottky-pn diode in forward bias. Diamond and Related Materials, 2018, 85, 49-52.	1.8	11
148	Characterization of Schottky Barrier Diodes on Heteroepitaxial Diamond on 3C-SiC/Si Substrates. IEEE Transactions on Electron Devices, 2020, 67, 212-216.	1.6	11
149	Insight into Al2O3/B-doped diamond interface states with high-temperature conductance method. Applied Physics Letters, 2020, 117, .	1.5	11
150	Fabrication of inversion p-channel MOSFET with a nitrogen-doped diamond body. Applied Physics Letters, 2021, 119, .	1.5	11
151	Chlorosilane adsorption on clean Si surfaces: Scanning tunneling microscopy and Fourier-transform infrared absorption spectroscopy studies. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2001, 19, 2001-2006.	0.9	10
152	Analysis of selective growth of n-type diamond in lateral pâ€“n junction diodes by cross-sectional transmission electron microscopy. Japanese Journal of Applied Physics, 2014, 53, 05FP01.	0.8	10
153	Influence of substrate misorientation on the surface morphology of homoepitaxial diamond (111) films. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 2051-2055.	0.8	10
154	Dynamic properties of diamond high voltage pâ€“iâ€“n diodes. Japanese Journal of Applied Physics, 2017, 56, 04CR14.	0.8	10
155	Charge-state control of ensemble of nitrogen vacancy centers by nâ€“iâ€“n diamond junctions. Applied Physics Express, 2018, 11, 033004.	1.1	10
156	Nuclear-magnetic-resonance study of amorphous silicon-hydrogen-phosphorus alloys. Physical Review B, 1988, 38, 31-38.	1.1	9
157	STM and Raman study of the evolution of the surface morphology in Î¼c-Si:H. Journal of Non-Crystalline Solids, 1996, 198-200, 863-866.	1.5	9
158	In vacuo electron-spin-resonance study on amorphous fluorinated carbon films for understanding of surface chemical reactions in plasma etching. Applied Physics Letters, 2002, 81, 1773-1775.	1.5	9
159	Efficiency of multiple atom doping in wide band gap semiconductors. Applied Physics Letters, 2005, 86, 261910.	1.5	9
160	Passivation effects of deuterium exposure on boron-doped CVD homoepitaxial diamond. Diamond and Related Materials, 2005, 14, 2023-2026.	1.8	9
161	Etching Damage in Diamond Studied Using an Energy-Controlled Oxygen Ion Beam. Japanese Journal of Applied Physics, 2007, 46, 60-64.	0.8	9
162	Energy-loss mechanism of single-crystal silicon microcantilever due to surface defects generated during plasma processing. Journal of Micromechanics and Microengineering, 2013, 23, 065020.	1.5	9

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163	Inversion channel MOSFET on heteroepitaxially grown free-standing diamond. Carbon, 2021, 175, 615-619.	5.4	9
164	A New Model for the Carrier Transport in Amorphous Si: H Schottky Barrier Diodes. Japanese Journal of Applied Physics, 1980, 19, 131.	0.8	8
165	Selective Area Growth of Si on Thin Insulating Layers for Nanostructure Fabrication. Japanese Journal of Applied Physics, 1998, 37, L1087-L1089.	0.8	8
166	Effects of Chemical Composition and Morphology of Substrate Surfaces on Crystallinity of Ultrathin Hydrogenated Microcrystalline Silicon Films. Japanese Journal of Applied Physics, 2000, 39, 6647-6651.	0.8	8
167	Exciton-derived Electron Emission from (001) Diamondpâ€“nJunction Diodes with Negative Electron Affinity. Applied Physics Express, 2008, 1, 015004.	1.1	8
168	Ab initio dynamics of field emission from diamond surfaces. Applied Physics Letters, 2013, 103, .	1.5	8
169	Insight into temperature impact of Ta filaments on high-growth-rate diamond (100) films by hot-filament chemical vapor deposition. Diamond and Related Materials, 2021, 118, 108515.	1.8	8
170	Structural Differences between Hydrogenated and Deuterated Amorphous Silicon Films Prepared by Plasma-Enhanced Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1991, 30, L142-L144.	0.8	7
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